



PRELIMINARY

CY7C1041V33

256K x 16 Static RAM

Features

- High speed
 - $t_{AA} = 15 \text{ ns}$
- Low active power
 - 612 mW (max.)
- Low CMOS standby power (Commercial L version)
 - 720 μW (max.)
- 2.0V Data Retention (400 μW at 2.0V retention)
- Automatic power-down when deselected
- TTL-compatible inputs and outputs
- Easy memory expansion with CE and OE features

Functional Description

The CY7C1041V33 is a high-performance CMOS static RAM organized as 262,144 words by 16 bits.

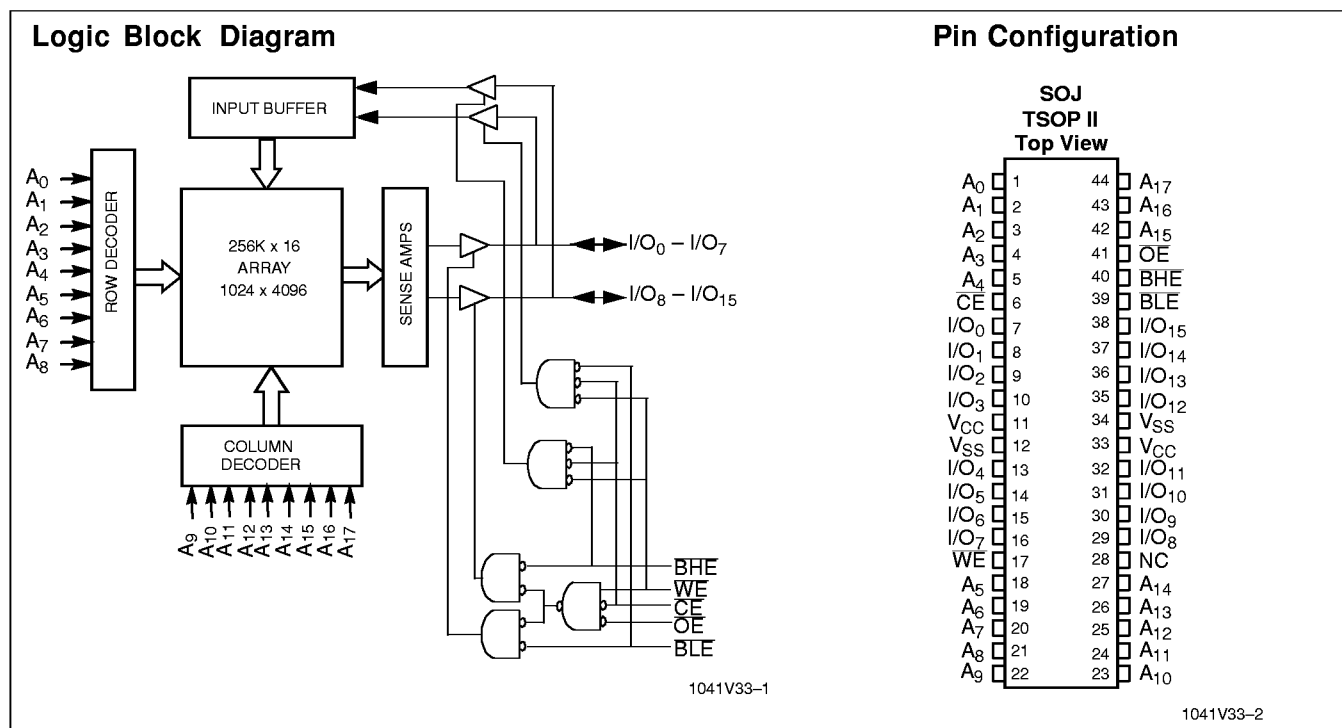
Writing to the device is accomplished by taking chip enable ($\overline{\text{CE}}$) and write enable ($\overline{\text{WE}}$) inputs LOW. If byte low enable ($\overline{\text{BLE}}$) is LOW, then data from I/O pins (I/O_0 through I/O_7), is

written into the location specified on the address pins (A_0 through A_{17}). If byte high enable ($\overline{\text{BHE}}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{17}).

Reading from the device is accomplished by taking chip enable ($\overline{\text{CE}}$) and output enable ($\overline{\text{OE}}$) LOW while forcing the write enable ($\overline{\text{WE}}$) HIGH. If byte low enable ($\overline{\text{BLE}}$) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7 . If byte high enable ($\overline{\text{BHE}}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15} . See the truth table at the back of this datasheet for a complete description of read and write modes.

The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when the device is deselected ($\overline{\text{CE}}$ HIGH), the outputs are disabled ($\overline{\text{OE}}$ HIGH), the $\overline{\text{BHE}}$ and $\overline{\text{BLE}}$ are disabled ($\overline{\text{BHE}}$, $\overline{\text{BLE}}$ HIGH), or during a write operation ($\overline{\text{CE}}$ LOW, and $\overline{\text{WE}}$ LOW).

The CY7C1041V33 is available in a standard 44-pin 400-mil-wide body width SOJ and 44-pin TSOP II package with center power and ground (revolutionary) pinout.



Selection Guide

	7C1041V33-12	7C1041V33-15	7C1041V33-20	7C1041V33-25
Maximum Access Time (ns)	12	15	20	25
Maximum Operating Current (mA)	190	170	150	130
Maximum CMOS Standby Current (mA)	Com'l/Ind'l	8	8	8
	Com'l L	0.5	0.5	0.5

Shaded areas contain advance information.



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C

Ambient Temperature with Power Applied -55°C to +125°C

Supply Voltage on V_{CC} to Relative GND^[1] -0.5V to +4.6V

DC Voltage Applied to Outputs in High Z State^[1] -0.5V to V_{CC} +0.5V

DC Input Voltage^[1] -0.5V to V_{CC} +0.5V

Current into Outputs (LOW) 20 mA

Operating Range

Range	Ambient Temperature ^[2]	V _{CC}
Commercial	0°C to +70°C	3.3V ± 0.3V
Industrial	-40°C to +85°C	

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	7C1041-12V33		7C1041V33-15		Unit		
			Min.	Max.	Min.	Max.			
V _{OH}	Output HIGH Voltage	V _{CC} = Min., I _{OH} = -4.0 mA	2.4		2.4		V		
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 8.0 mA		0.4		0.4	V		
V _{IH}	Input HIGH Voltage		2.2	V _{CC} + 0.5	2.2	V _{CC} + 0.5	V		
V _{IL}	Input LOW Voltage ^[1]		-0.5	0.8	-0.5	0.8	V		
I _{IX}	Input Load Current	GND ≤ V _I ≤ V _{CC}	-1	+1	-1	+1	μA		
I _{OZ}	Output Leakage Current	GND ≤ V _{OUT} ≤ V _{CC} , Output Disabled	-1	+1	-1	+1	μA		
I _{CC}	V _{CC} Operating Supply Current	V _{CC} = Max., f = f _{MAX} = 1/t _{RC}		190		170	mA		
I _{SB1}	Automatic CE Power-Down Current —TTL Inputs	Max. V _{CC} , CE ≥ V _{IH} V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX}		40		40	mA		
I _{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V _{CC} , CE ≥ V _{CC} - 0.3V, V _{IN} ≥ V _{CC} - 0.3V, or V _{IN} ≤ 0.3V, f=0	Com'l/Ind'l			8		8	mA
			Com'l	L		0.5		0.5	mA

Shaded areas contain advance information.

Notes:

- V_{IL} (min.) = -2.0V for pulse durations of less than 20 ns.
- T_A is the "instant on" case temperature.

Electrical Characteristics Over the Operating Range (continued)

Parameter	Description	Test Conditions	7C1041V33-20		7C1041V33-25		Unit
			Min.	Max.	Min.	Max.	
V _{OH}	Output HIGH Voltage	V _{CC} = Min., I _{OH} = -4.0 mA	2.4		2.4		V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 8.0 mA		0.4		0.4	V
V _{IH}	Input HIGH Voltage		2.2	V _{CC} + 0.5	2.2	V _{CC} + 0.5	V
V _{IL}	Input LOW Voltage ^[1]		-0.5	0.8	-0.5	0.8	V
I _{IX}	Input Load Current	GND ≤ V _I ≤ V _{CC}	-1	+1	-1	+1	μA
I _{OZ}	Output Leakage Current	GND ≤ V _{OUT} ≤ V _{CC} , Output Disabled	-1	+1	-1	+1	μA
I _{CC}	V _{CC} Operating Supply Current	V _{CC} = Max., f = f _{MAX} = 1/t _{RC}		150		130	mA
I _{SB1}	Automatic CE Power-Down Current —TTL Inputs	Max. V _{CC} , CE ≥ V _{IH} V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX}		40		40	mA
I _{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V _{CC} , CE ≥ V _{CC} - 0.3V, V _{IN} ≥ V _{CC} - 0.3V, or V _{IN} ≤ 0.3V, f=0	Com'I/Ind'I				
			Com'I	L		8	
				0.5		0.5	mA

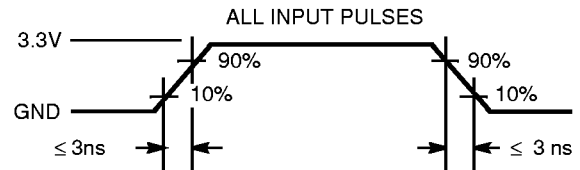
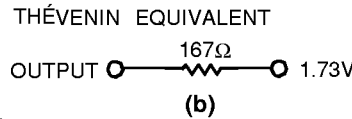
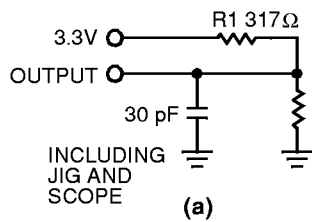
Capacitance^[3]

Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz, V _{CC} = 3.3V	8	pF
C _{OUT}	I/O Capacitance		8	pF

Note:

3. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms





Switching Characteristics^[4] Over the Operating Range

Parameter	Description	7C1041V33-12		7C1041V33-15		Unit
		Min.	Max.	Min.	Max.	
READ CYCLE						
t _{RC}	Read Cycle Time	12		15		ns
t _{AA}	Address to Data Valid		12		15	ns
t _{OHA}	Data Hold from Address Change	3		3		ns
t _{ACE}	\overline{CE} LOW to Data Valid		12		15	ns
t _{DOE}	\overline{OE} LOW to Data Valid		6		7	ns
t _{LZOE}	\overline{OE} LOW to Low Z	0		0		ns
t _{HZOE}	\overline{OE} HIGH to High Z ^[5, 6]		6		7	ns
t _{LZCE}	\overline{CE} LOW to Low Z ^[6]	3		3		ns
t _{HZCE}	\overline{CE} HIGH to High Z ^[5, 6]		6		7	ns
t _{PU}	\overline{CE} LOW to Power-Up	0		0		ns
t _{PD}	\overline{CE} HIGH to Power-Down		12		15	ns
t _{DBE}	Byte enable to Data Valid		6		7	ns
t _{LZBE}	Byte enable to Low Z	0		0		ns
t _{HZBE}	Byte disable to High Z		6		7	ns
WRITE CYCLE^[7,8]						
t _{WC}	Write Cycle Time	12		15		ns
t _{SCE}	\overline{CE} LOW to Write End	10		12		ns
t _{AW}	Address Set-Up to Write End	10		12		ns
t _{HA}	Address Hold from Write End	0		0		ns
t _{SA}	Address Set-Up to Write Start	0		0		ns
t _{PWE}	WE Pulse Width	10		12		ns
t _{SD}	Data Set-Up to Write End	7		8		ns
t _{HD}	Data Hold from Write End	0		0		ns
t _{LZWE}	WE HIGH to Low Z ^[6]	3		3		ns
t _{HZWE}	WE LOW to High Z ^[5, 6]		6		7	ns
t _{BW}	Byte Enable to End of Write	10		12		ns

Shaded areas contain advance information.

Notes:

- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
- t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
- At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
- The internal write time of the memory is defined by the overlap of \overline{CE} LOW, and WE LOW. \overline{CE} and WE must be LOW to initiate a write, and the transition of either of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
- The minimum write cycle time for Write Cycle no. 3 (WE controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{SD}.



Switching Characteristics^[4] Over the Operating Range (continued)

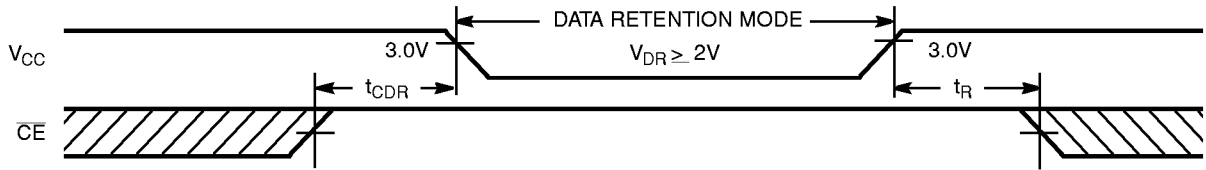
Parameter	Description	CY7C1041V33-20		CY7C1041V33-25		Unit
		Min.	Max.	Min.	Max.	
READ CYCLE						
t _{RC}	Read Cycle Time	20		25		ns
t _{AA}	Address to Data Valid		20		25	ns
t _{OHA}	Data Hold from Address Change	3		5		ns
t _{ACE}	CE LOW to Data Valid		20		25	ns
t _{DOE}	OE LOW to Data Valid		8		10	ns
t _{LZOE}	OE LOW to Low Z	0		0		ns
t _{HZOE}	OE HIGH to High Z ^[5, 6]		8		10	ns
t _{LZCE}	CE LOW to Low Z ^[6]	3		5		ns
t _{HZCE}	CE HIGH to High Z ^[5, 6]		8		10	ns
t _{PU}	CE LOW to Power-Up	0		0		ns
t _{PD}	CE HIGH to Power-Down		20		25	ns
t _{DBE}	Byte enable to Data Valid		8		10	ns
t _{LZBE}	Byte enable to Low Z	0		0		ns
t _{HZBE}	Byte disable to High Z		8		10	ns
WRITE CYCLE ^[7,8]						
t _{WC}	Write Cycle Time	20		25		ns
t _{SCE}	CE LOW to Write End	13		15		ns
t _{AW}	Address Set-Up to Write End	13		15		ns
t _{HA}	Address Hold from Write End	0		0		ns
t _{SA}	Address Set-Up to Write Start	0		0		ns
t _{PWE}	WE Pulse Width	13		15		ns
t _{SD}	Data Set-Up to Write End	9		10		ns
t _{HD}	Data Hold from Write End	0		0		ns
t _{LZWE}	WE HIGH to Low Z ^[6]	3		5		ns
t _{HZWE}	WE LOW to High Z ^[5, 6]		8		10	ns
t _{BW}	Byte enable to end of write	13		15		ns

Data Retention Characteristics Over the Operating Range

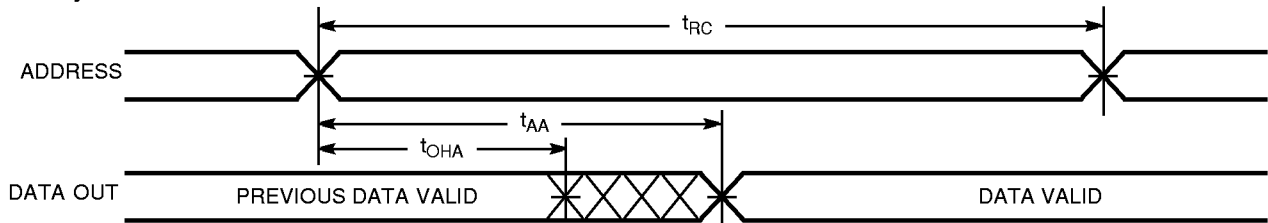
Parameter	Description	Conditions ^[10]	Min.	Max.	Unit
V _{DR}	V _{CC} for Data Retention		2.0		V
I _{CCDR}	Data Retention Current	V _{CC} = V _{DR} = 3.0V, CE ≥ V _{CC} - 0.3V, V _{IN} ≥ V _{CC} - 0.3V or V _{IN} ≤ 0.3V		500	μA
t _{CDR} ^[9]	Chip Deselect to Data Retention Time		0		ns
t _R ^[9]	Operation Recovery Time		t _{RC}		ns

Notes:

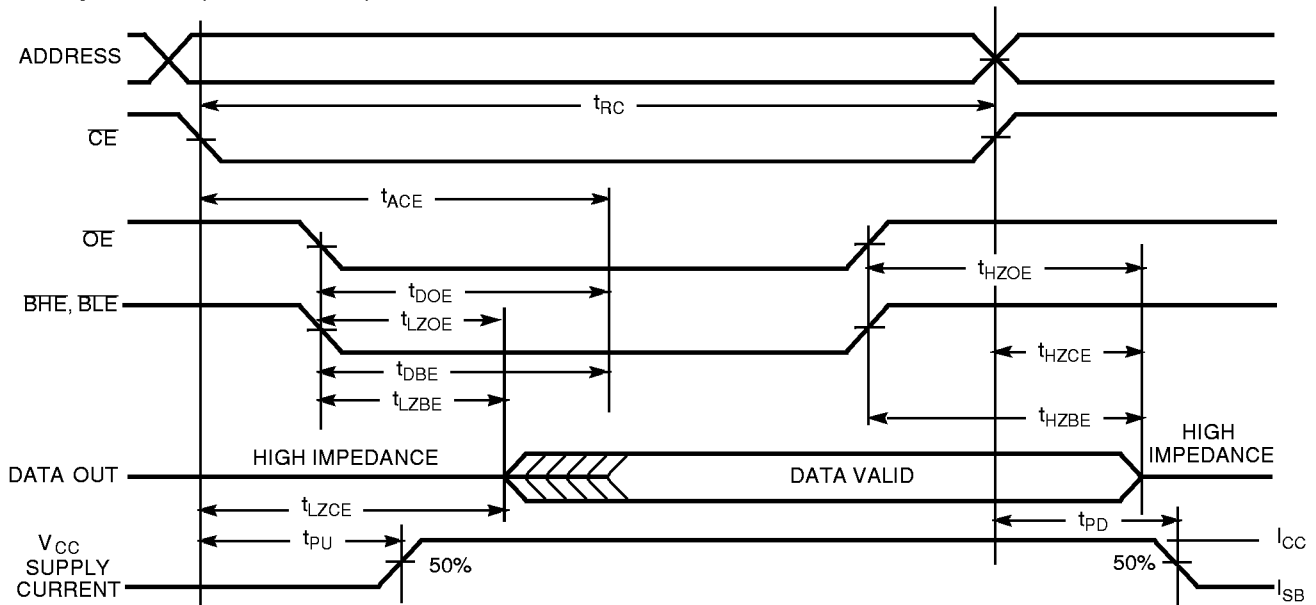
- 9. t_r ≤ 3 ns for the -12 and -15 speeds. t_r ≤ 5 ns for the -20 and slower speeds.
- 10. No input may exceed V_{CC} + 0.5V.

Data Retention Waveform


1041V33-5

Switching Waveforms
Read Cycle No.1 ^[11, 12]


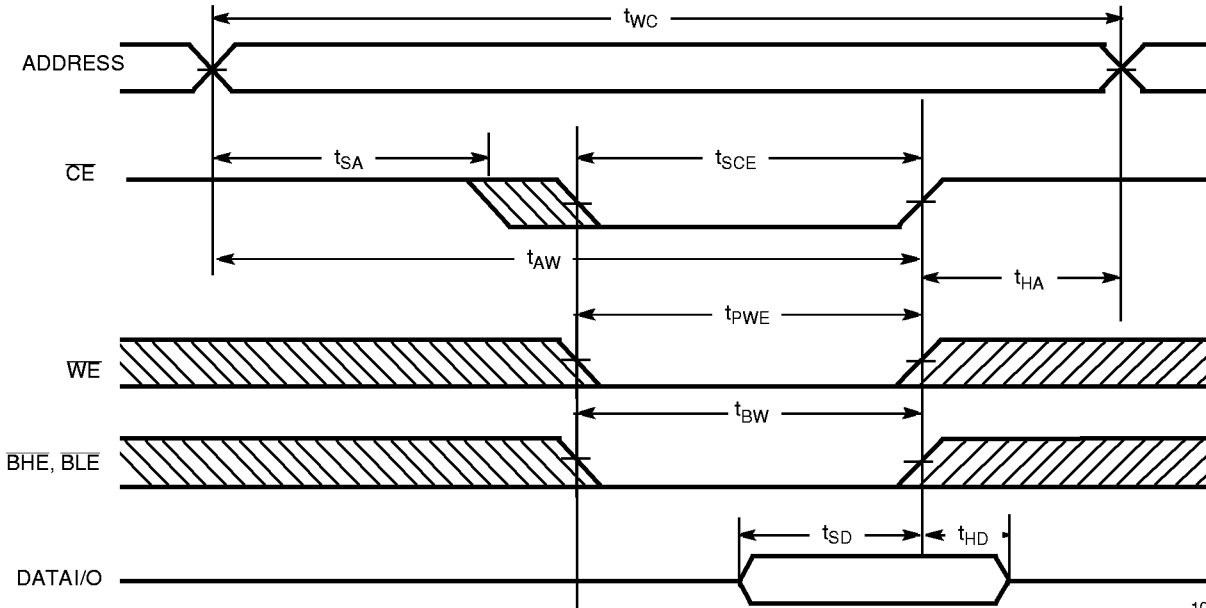
1041V33-6

Read Cycle No.2 (\overline{OE} Controlled) ^[12, 13]


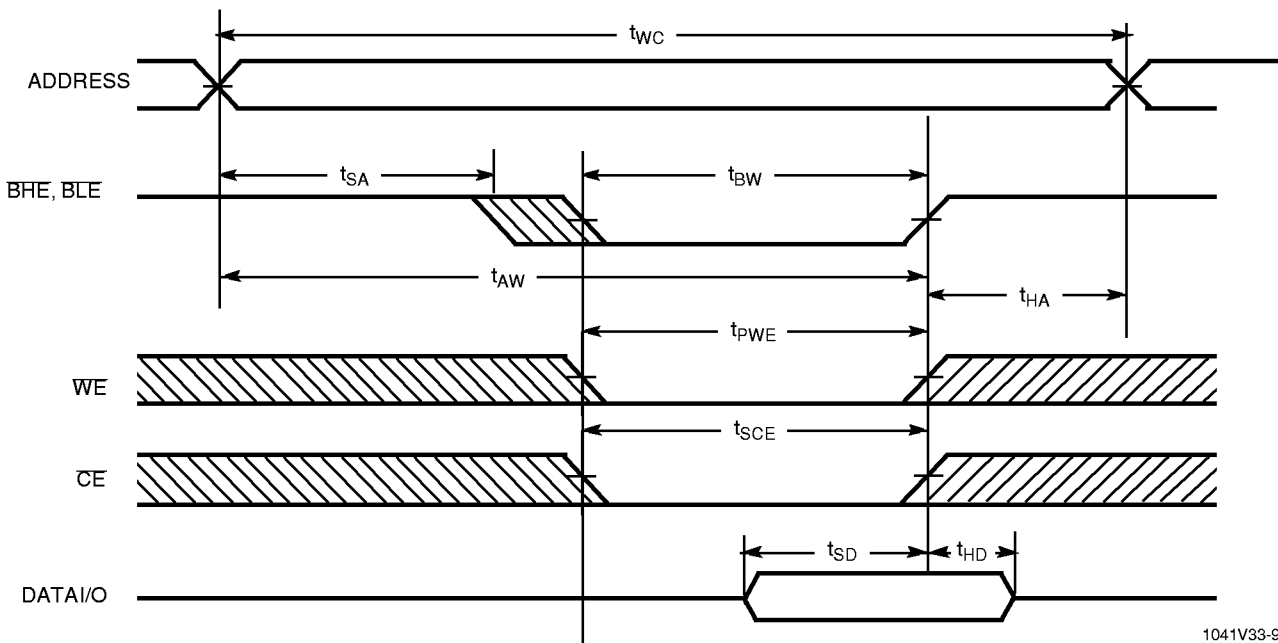
1041V33-7

Notes:

11. Device is continuously selected. \overline{OE} , \overline{CE} , BHE and/or BHE = V_{IL} .
12. \overline{WE} is HIGH for read cycle.
13. Address valid prior to or coincident with \overline{CE} transition LOW.

Switching Waveforms (continued)
Write Cycle No. 1 (\overline{CE} Controlled)^[14, 15]


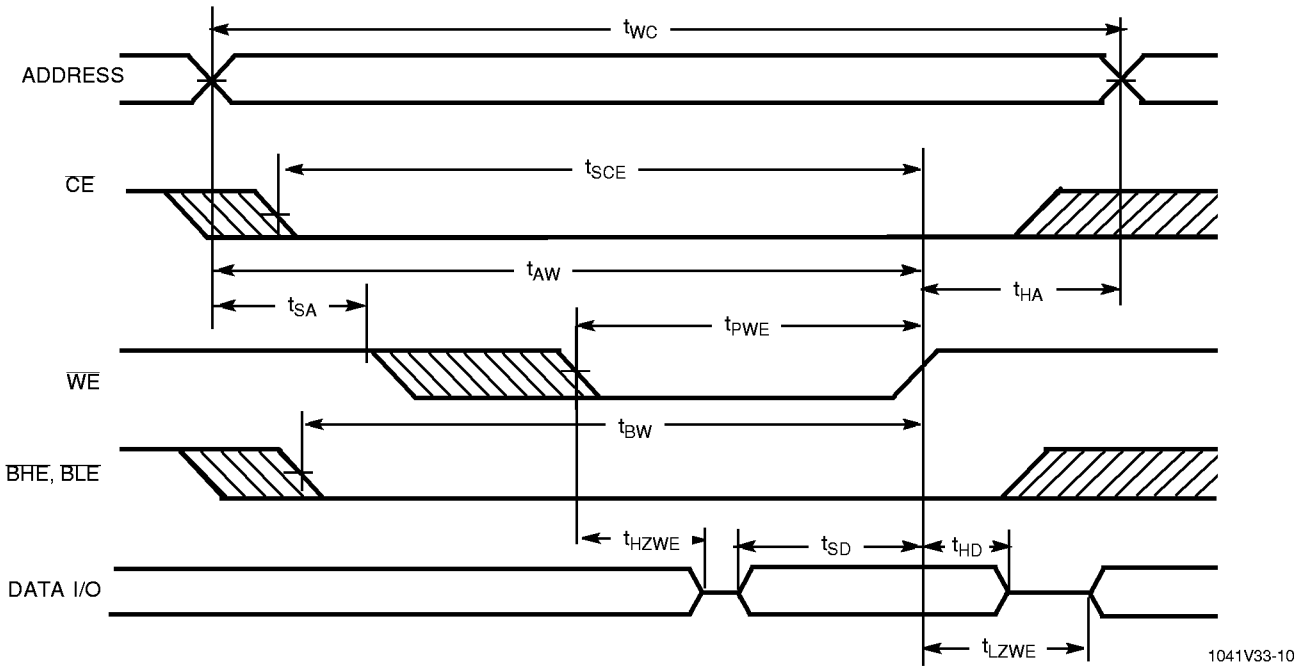
1041V33-8

Write Cycle No. 2 (BLE or BHE Controlled)


1041V33-9

Notes:

14. Data I/O is high impedance if \overline{OE} or BHE and/or BLE = V_{IH} .
15. If \overline{CE} goes HIGH simultaneously with WE going HIGH, the output remains in a high-impedance state.

Switching Waveforms (continued)
Write Cycle No.3 (WE Controlled, OE LOW)


1041V33-10

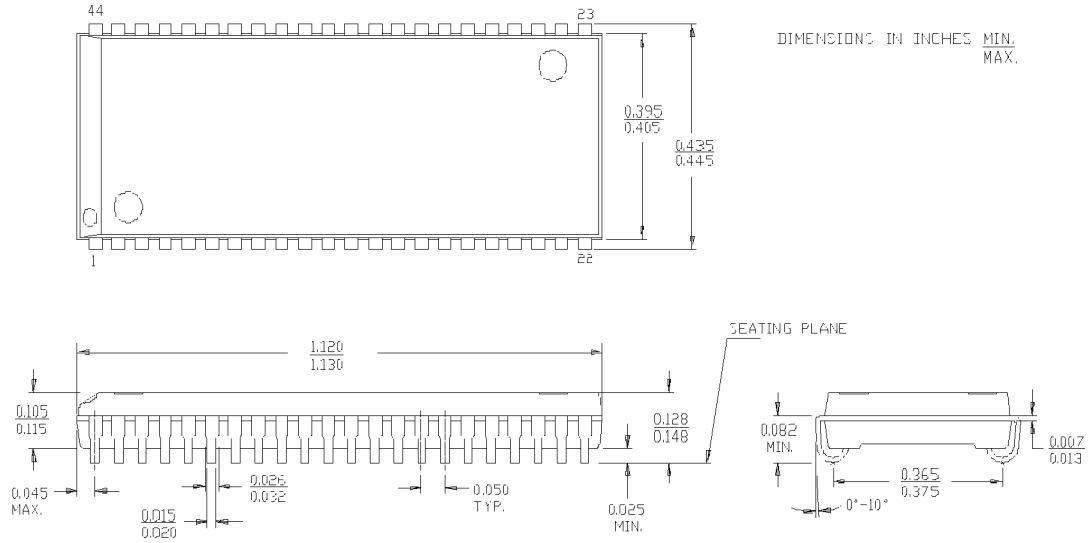
Truth Table

CE	OE	WE	BLE	BHE	I/O ₀ -I/O ₇	I/O ₈ -I/O ₁₅	Mode	Power
H	X	X	X	X	High Z	High Z	Power Down	Standby (I_{SB})
L	L	H	L	L	Data Out	Data Out	Read All bits	Active (I_{CC})
L	L	H	L	H	Data Out	High Z	Read Lower bits only	Active (I_{CC})
L	L	H	H	L	High Z	Data Out	Read Upper bits only	Active (I_{CC})
L	X	L	L	L	Data In	Data In	Write All bits	Active (I_{CC})
L	X	L	L	H	Data In	High Z	Write Lower bits only	Active (I_{CC})
L	X	L	H	L	High Z	Data In	Write Upper bits only	Active (I_{CC})
L	H	H	X	X	High Z	High Z	Selected, Outputs Disabled	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C1041V33 -15VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1041V33L-15VC	V34	44-Lead (400-Mil) Molded SOJ	
	CY7C1041V33 -15ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041V33L-15ZC	Z44	44-Pin TSOP II Z44	
20	CY7C1041V33L-20VC	V34	44-Lead (400-Mil) Molded SOJ	
	CY7C1041V33-20ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041V33L-20ZC	Z44	44-Pin TSOP II Z44	
25	CY7C1041V33L-25VC	V34	44-Lead (400-Mil) Molded SOJ	

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Package Diagrams
44-Lead (400-Mil) Molded SOJ V34

44-Pin TSOP II Z44

DIMENSIONS IN MM (INCH)
MAX
MIN
LEAD COPLANARITY 0.004 INCHES.

